

650V SuperJunction Power MOSFET

Features

- g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Product Summary

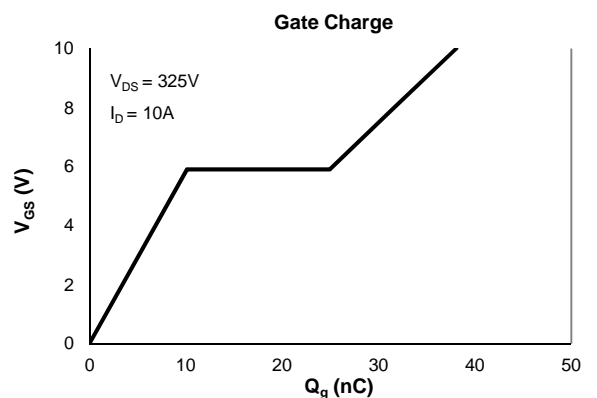
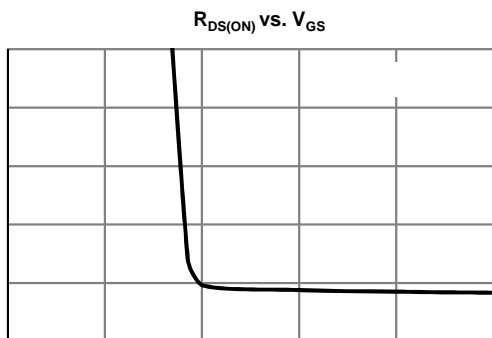
Parameter	Value	Unit
V _{DS}	650	V
V _{GS}	3.5	V
I _{DM}	17.4	A
E _{AS}	169	mJ
E _{oss@400V}	5.2	J

Applications

Ordering Information

Device	Package	# of Pins	Marking	MSL	T _J (°C)	Media	Quantity (pcs)
	DFN8080-4L	4	H65R190A	1	-55 to 150	13-inch Reel	3000

Symbol	Unit
V _{DS}	V
V _{GS}	V
I _{DM}	A
I _{AS}	A
E _{AS}	mJ
D _B	(%) *
T _J	



	Symbol	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	$V_{(BR)DSS}$	650			V
	I_{DSS}			1.0	A
	I_{GSS}			±100	nA
	$V_{GS(th)}$	2.5	3.5	4.5	V
	$R_{DS(ON)}$		169	190	m
	V_{SD}		0.75	1.0	V
	I_S			156	A
	C_{ISS}		1560		pF
	C_{OSS}				

Typical Electrical & Thermal Characteristics

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